## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet



Semiconductor

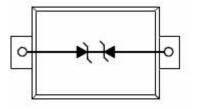


#### **Applications**

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

#### **Features**

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 200 Watts @ 8 x 20 \_s Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection



SOD- 523

#### **ORDERING INFORMATION**

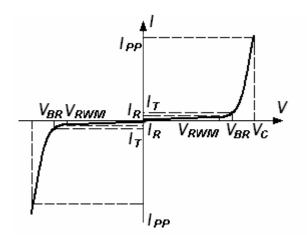
Device	Package	Shipping
MSESD5D3V3C	SOD-523	3000/Tape & Reel

#### Absolute Ratings (T<sub>amb</sub>=25°C)

Symbol	Parameter	Value	Units	
P <sub>PP</sub>	Peak Pulse Power (t <sub>p</sub> = 8/20 μ s)	200	W	
T <sub>L</sub>	Maximum lead temperature for soldering during	260	°C	
T <sub>stg</sub>	Storage Temperature Range	-55 to +155	°C	
T <sub>op</sub>	Operating Temperature Range	-40 to +125	°C	
Tj	Maximum junction temperature		150	°C
	IEC61000-4-2 (ESD)	air discharge contact discharge	±15 ±8	KV
	IEC61000-4-4 (EFT)		40	Α
	ESD Voltage P	er Human Body Model	16	KV

#### **Electrical Parameter**

Symbol	Parameter					
Symbol	1 drufficter					
$I_{PP}$	Maximum Reverse Peak Pulse Current					
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>					
$V_{RWM}$	Working Peak Reverse Voltage					
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>					
I <sub>T</sub>	Test Current					
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>					



#### Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.VF = 0.9V at IF = 10mA

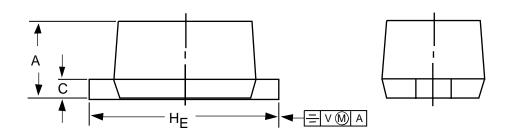
Device	V <sub>RWM</sub> (V)	I <sub>R</sub> (uA) @ V <sub>RWM</sub>	V <sub>BR</sub> (V)@ I <sub>T</sub> (Note 1)	I <sub>T</sub>	V <sub>C</sub> (V) @ I <sub>PP</sub> =5 A*	V <sub>C</sub> (V) @ Max I <sub>PP</sub> *	I <sub>PP</sub> (A)*	P <sub>PK</sub> (W)*	C (pF)
	Max	Max	Min	mA	Тур	Max	Max	Max	Тур
MSESD5D3V3C	3.3	1	5.0	1.0	11.6	18.6	9.4	174	25

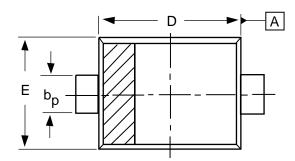
<sup>\*</sup>Surge current waveform per Figure 1.

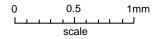
<sup>1.</sup>  $V_{BR}$  is measured with a pluse test current  $I_T$  at an ambient temperature of 25  $^\circ\!\! {
m C}$  .



#### **SOD-523**







### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	b <sub>p</sub>	С	D	E	Η <sub>E</sub>	V
m m	0.7	0.35	0.2	1.3	0.9	1.7	0.15
	0.5	0.25	0.1	1.1	0.7	1.5	0.13

#### Note

1. The marking bar indicates the cathode.



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